

# STARPOWER

## SEMICONDUCTOR

## IGBT

# GD100FFY120C6SF

**1200V/100A 6 in one-package**

## General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.



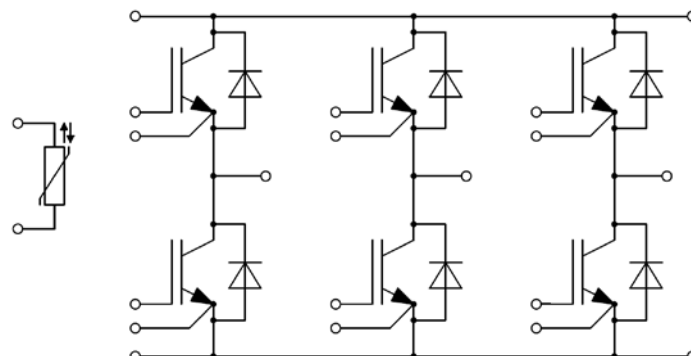
## Features

- Low  $V_{CE(sat)}$  Trench IGBT technology
- 10 $\mu$ s short circuit capability
- $V_{CE(sat)}$  with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology
- PressFIT contact technology

## Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

## Equivalent Circuit Schematic



**Absolute Maximum Ratings**  $T_C=25^{\circ}\text{C}$  unless otherwise noted**IGBT**

| Symbol    | Description                                                                 | Value      | Unit |
|-----------|-----------------------------------------------------------------------------|------------|------|
| $V_{CES}$ | Collector-Emitter Voltage                                                   | 1200       | V    |
| $V_{GES}$ | Gate-Emitter Voltage                                                        | $\pm 20$   | V    |
| $I_C$     | Collector Current @ $T_C=25^{\circ}\text{C}$<br>@ $T_C=100^{\circ}\text{C}$ | 155<br>100 | A    |
| $I_{CM}$  | Pulsed Collector Current $t_p=1\text{ms}$                                   | 200        | A    |
| $P_D$     | Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$                       | 511        | W    |

**Diode**

| Symbol    | Description                                    | Value | Unit |
|-----------|------------------------------------------------|-------|------|
| $V_{RRM}$ | Repetitive Peak Reverse Voltage                | 1200  | V    |
| $I_F$     | Diode Continuous Forward Current               | 100   | A    |
| $I_{FM}$  | Diode Maximum Forward Current $t_p=1\text{ms}$ | 200   | A    |

**Module**

| Symbol     | Description                                              | Value       | Unit               |
|------------|----------------------------------------------------------|-------------|--------------------|
| $T_{jmax}$ | Maximum Junction Temperature                             | 175         | $^{\circ}\text{C}$ |
| $T_{jop}$  | Operating Junction Temperature                           | -40 to +150 | $^{\circ}\text{C}$ |
| $T_{STG}$  | Storage Temperature Range                                | -40 to +125 | $^{\circ}\text{C}$ |
| $V_{ISO}$  | Isolation Voltage RMS, $f=50\text{Hz}$ , $t=1\text{min}$ | 4000        | V                  |

**IGBT Characteristics**  $T_C=25^{\circ}\text{C}$  unless otherwise noted

| Symbol        | Parameter                               | Test Conditions                                                                                                     | Min. | Typ. | Max. | Unit     |
|---------------|-----------------------------------------|---------------------------------------------------------------------------------------------------------------------|------|------|------|----------|
| $V_{CE(sat)}$ | Collector to Emitter Saturation Voltage | $I_C=100\text{A}, V_{GE}=15\text{V}, T_j=25^{\circ}\text{C}$                                                        |      | 1.70 | 2.15 | V        |
|               |                                         | $I_C=100\text{A}, V_{GE}=15\text{V}, T_j=125^{\circ}\text{C}$                                                       |      | 1.95 |      |          |
|               |                                         | $I_C=100\text{A}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}$                                                       |      | 2.00 |      |          |
| $V_{GE(th)}$  | Gate-Emitter Threshold Voltage          | $I_C=4.0\text{mA}, V_{CE}=V_{GE}, T_j=25^{\circ}\text{C}$                                                           | 5.3  | 5.8  | 6.3  | V        |
| $I_{CES}$     | Collector Cut-Off Current               | $V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$                                                          |      |      | 1.0  | mA       |
| $I_{GES}$     | Gate-Emitter Leakage Current            | $V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^{\circ}\text{C}$                                                          |      |      | 100  | nA       |
| $R_{Gint}$    | Internal Gate Resistance                |                                                                                                                     |      | 7.5  |      | $\Omega$ |
| $t_{d(on)}$   | Turn-On Delay Time                      | $V_{CC}=600\text{V}, I_C=100\text{A}, R_G=1.6\Omega, V_{GE}=\pm 15\text{V}, T_j=25^{\circ}\text{C}$                 |      | 170  |      | ns       |
| $t_r$         | Rise Time                               |                                                                                                                     |      | 32   |      | ns       |
| $t_{d(off)}$  | Turn-Off Delay Time                     |                                                                                                                     |      | 360  |      | ns       |
| $t_f$         | Fall Time                               |                                                                                                                     |      | 86   |      | ns       |
| $E_{on}$      | Turn-On Switching Loss                  |                                                                                                                     |      | 5.90 |      | mJ       |
| $E_{off}$     | Turn-Off Switching Loss                 |                                                                                                                     |      | 6.05 |      | mJ       |
| $t_{d(on)}$   | Turn-On Delay Time                      | $V_{CC}=600\text{V}, I_C=100\text{A}, R_G=1.6\Omega, V_{GE}=\pm 15\text{V}, T_j=125^{\circ}\text{C}$                |      | 180  |      | ns       |
| $t_r$         | Rise Time                               |                                                                                                                     |      | 42   |      | ns       |
| $t_{d(off)}$  | Turn-Off Delay Time                     |                                                                                                                     |      | 470  |      | ns       |
| $t_f$         | Fall Time                               |                                                                                                                     |      | 165  |      | ns       |
| $E_{on}$      | Turn-On Switching Loss                  |                                                                                                                     |      | 9.10 |      | mJ       |
| $E_{off}$     | Turn-Off Switching Loss                 |                                                                                                                     |      | 9.35 |      | mJ       |
| $t_{d(on)}$   | Turn-On Delay Time                      | $V_{CC}=600\text{V}, I_C=100\text{A}, R_G=1.6\Omega, V_{GE}=\pm 15\text{V}, T_j=150^{\circ}\text{C}$                |      | 181  |      | ns       |
| $t_r$         | Rise Time                               |                                                                                                                     |      | 43   |      | ns       |
| $t_{d(off)}$  | Turn-Off Delay Time                     |                                                                                                                     |      | 480  |      | ns       |
| $t_f$         | Fall Time                               |                                                                                                                     |      | 186  |      | ns       |
| $E_{on}$      | Turn-On Switching Loss                  |                                                                                                                     |      | 10.0 |      | mJ       |
| $E_{off}$     | Turn-Off Switching Loss                 |                                                                                                                     |      | 10.5 |      | mJ       |
| $I_{SC}$      | SC Data                                 | $t_P \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$ |      | 400  |      | A        |

**Diode Characteristics**  $T_C=25^{\circ}\text{C}$  unless otherwise noted

| Symbol    | Parameter                     | Test Conditions                                                                                                           | Min. | Typ. | Max. | Unit          |
|-----------|-------------------------------|---------------------------------------------------------------------------------------------------------------------------|------|------|------|---------------|
| $V_F$     | Diode Forward Voltage         | $I_F=100\text{A}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$                                                               |      | 1.70 | 2.15 | V             |
|           |                               | $I_F=100\text{A}, V_{GE}=0\text{V}, T_j=125^{\circ}\text{C}$                                                              |      | 1.65 |      |               |
|           |                               | $I_F=100\text{A}, V_{GE}=0\text{V}, T_j=150^{\circ}\text{C}$                                                              |      | 1.65 |      |               |
| $Q_r$     | Recovered Charge              | $V_R=600\text{V}, I_F=100\text{A},$<br>$-di/dt=2800\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$<br>$T_j=25^{\circ}\text{C}$  |      | 9.0  |      | $\mu\text{C}$ |
| $I_{RM}$  | Peak Reverse Recovery Current |                                                                                                                           |      | 110  |      | A             |
| $E_{rec}$ | Reverse Recovery Energy       |                                                                                                                           |      | 3.32 |      | mJ            |
| $Q_r$     | Recovered Charge              | $V_R=600\text{V}, I_F=100\text{A},$<br>$-di/dt=2800\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$<br>$T_j=125^{\circ}\text{C}$ |      | 16.2 |      | $\mu\text{C}$ |
| $I_{RM}$  | Peak Reverse Recovery Current |                                                                                                                           |      | 120  |      | A             |
| $E_{rec}$ | Reverse Recovery Energy       |                                                                                                                           |      | 5.70 |      | mJ            |
| $Q_r$     | Recovered Charge              | $V_R=600\text{V}, I_F=100\text{A},$<br>$-di/dt=2800\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$<br>$T_j=150^{\circ}\text{C}$ |      | 19.5 |      | $\mu\text{C}$ |
| $I_{RM}$  | Peak Reverse Recovery Current |                                                                                                                           |      | 123  |      | A             |
| $E_{rec}$ | Reverse Recovery Energy       |                                                                                                                           |      | 7.13 |      | mJ            |

**NTC Characteristics**  $T_C=25^{\circ}\text{C}$  unless otherwise noted

| Symbol       | Parameter              | Test Conditions                                        | Min. | Typ. | Max. | Unit       |
|--------------|------------------------|--------------------------------------------------------|------|------|------|------------|
| $R_{25}$     | Rated Resistance       |                                                        |      | 5.0  |      | k $\Omega$ |
| $\Delta R/R$ | Deviation of $R_{100}$ | $T_C=100^{\circ}\text{C}, R_{100}=493.3\Omega$         | -5   |      | 5    | %          |
| $P_{25}$     | Power Dissipation      |                                                        |      |      | 20.0 | mW         |
| $B_{25/50}$  | B-value                | $R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$  |      | 3375 |      | K          |
| $B_{25/80}$  | B-value                | $R_2=R_{25}\exp[B_{25/80}(1/T_2-1/(298.15\text{K}))]$  |      | 3411 |      | K          |
| $B_{25/100}$ | B-value                | $R_2=R_{25}\exp[B_{25/100}(1/T_2-1/(298.15\text{K}))]$ |      | 3433 |      | K          |

**Module Characteristics**  $T_C=25^{\circ}\text{C}$  unless otherwise noted

| Symbol        | Parameter                                | Min. | Typ.  | Max.  | Unit       |
|---------------|------------------------------------------|------|-------|-------|------------|
| $L_{CE}$      | Stray Inductance                         |      | 21    |       | nH         |
| $R_{CC'+EE'}$ | Module Lead Resistance, Terminal to Chip |      | 1.80  |       | m $\Omega$ |
| $R_{thJC}$    | Junction-to-Case (per IGBT)              |      |       | 0.293 | K/W        |
|               | Junction-to-Case (per Diode)             |      |       | 0.505 |            |
| $R_{thCH}$    | Case-to-Heatsink (per IGBT)              |      | 0.085 |       | K/W        |
|               | Case-to-Heatsink (per Diode)             |      | 0.147 |       |            |
|               | Case-to-Heatsink (per Module)            |      | 0.009 |       |            |
| $M$           | Mounting Torque, Screw M5                | 3.0  |       | 6.0   | N.m        |
| $G$           | Weight of Module                         |      | 300   |       | g          |

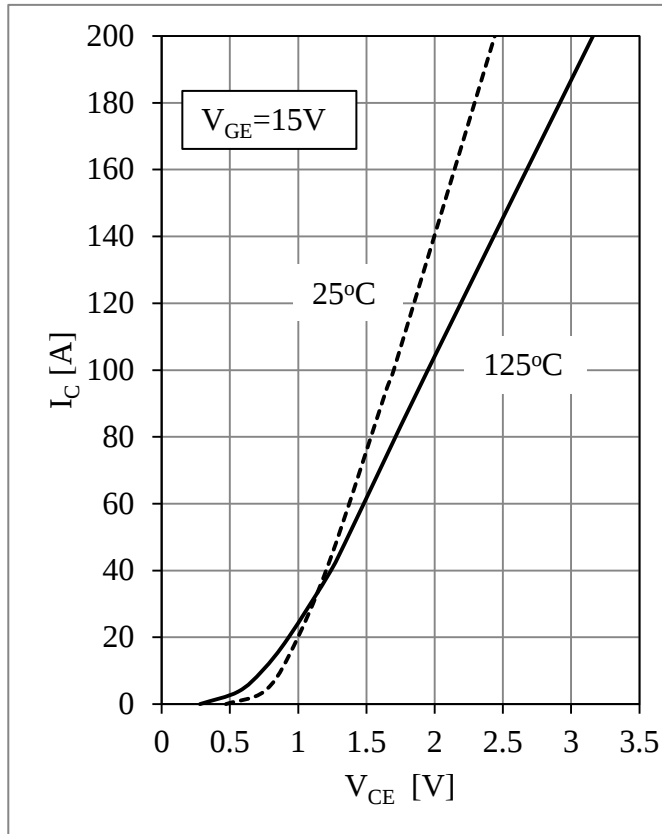


Fig 1. IGBT Output Characteristics

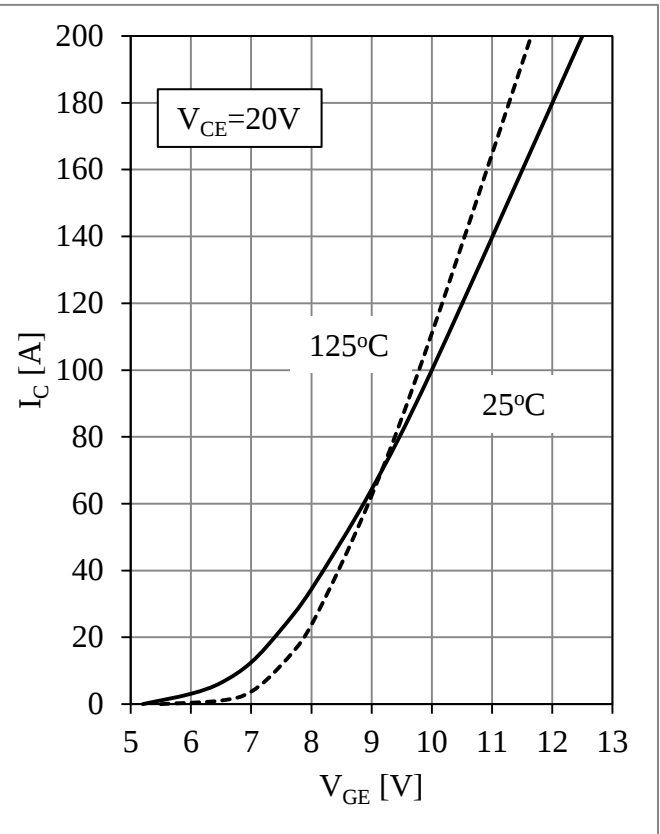
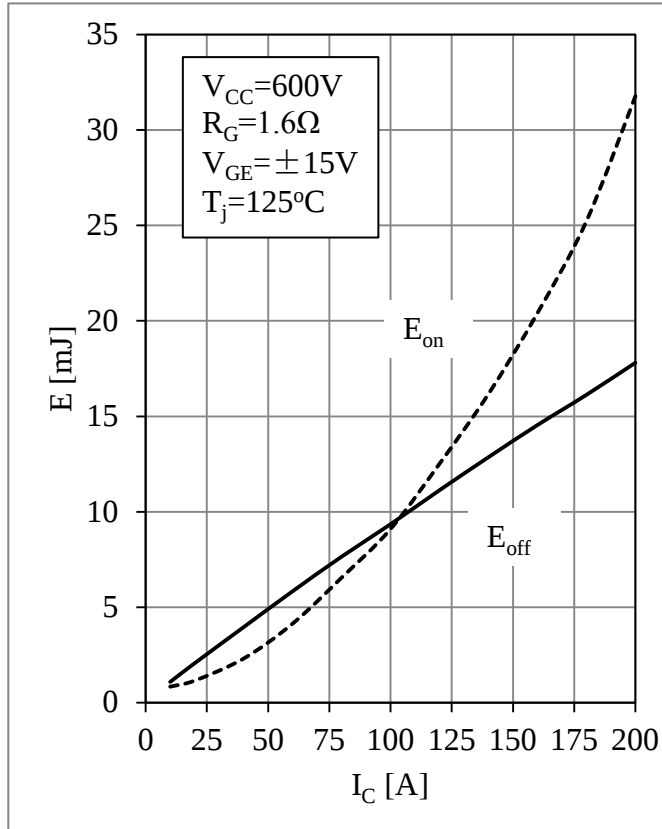
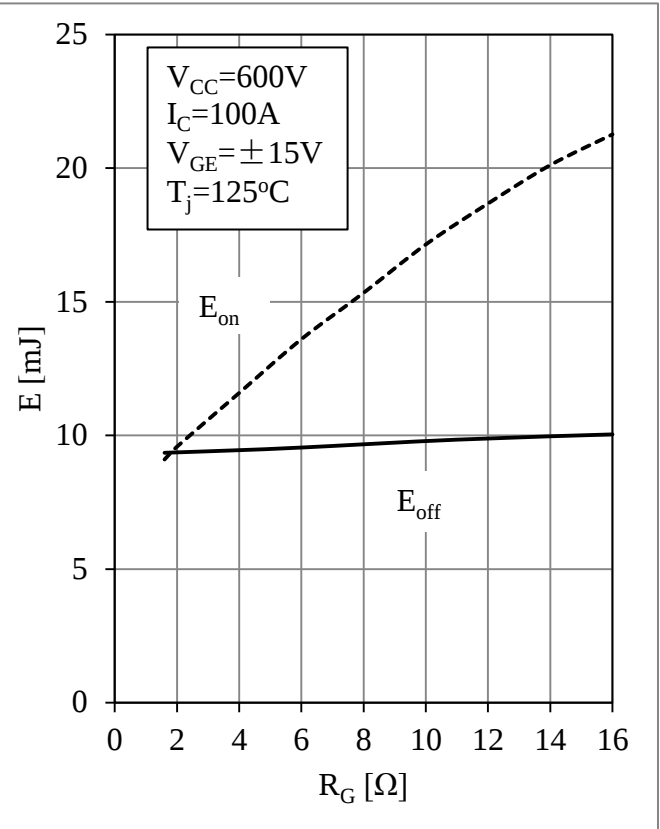


Fig 2. IGBT Transfer Characteristics

Fig 3. IGBT Switching Loss vs.  $I_C$ Fig 4. IGBT Switching Loss vs.  $R_G$

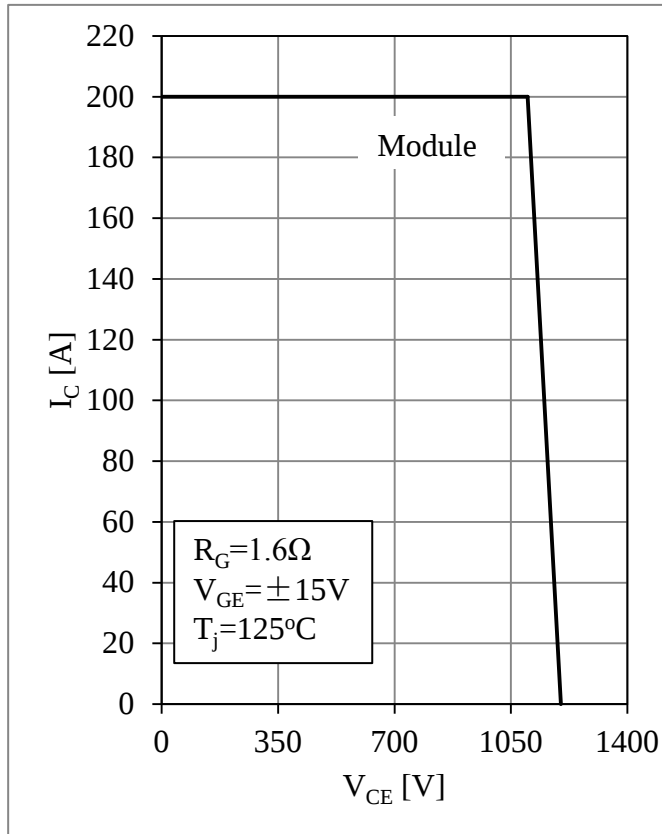


Fig 5. RBSOA

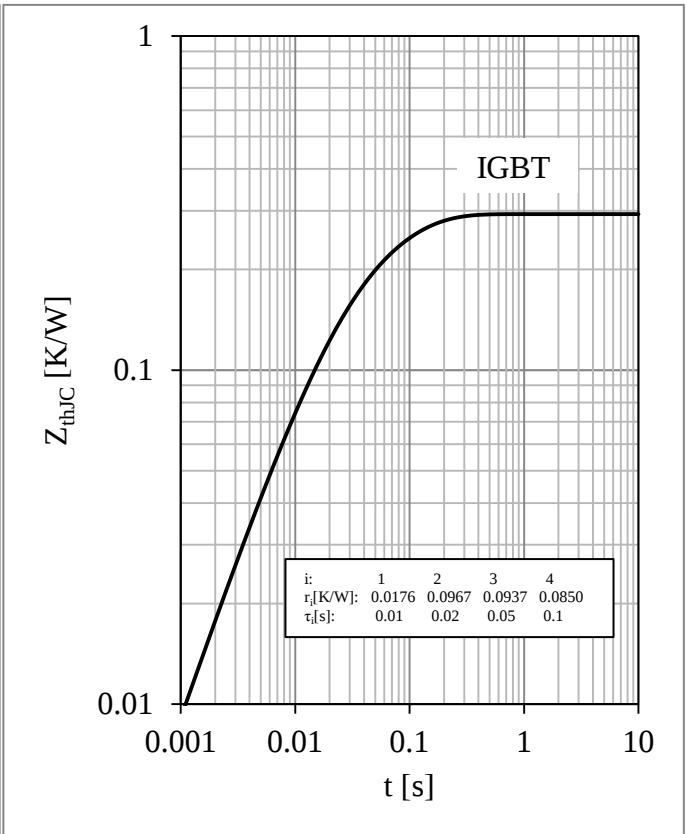


Fig 6. IGBT Transient Thermal Impedance

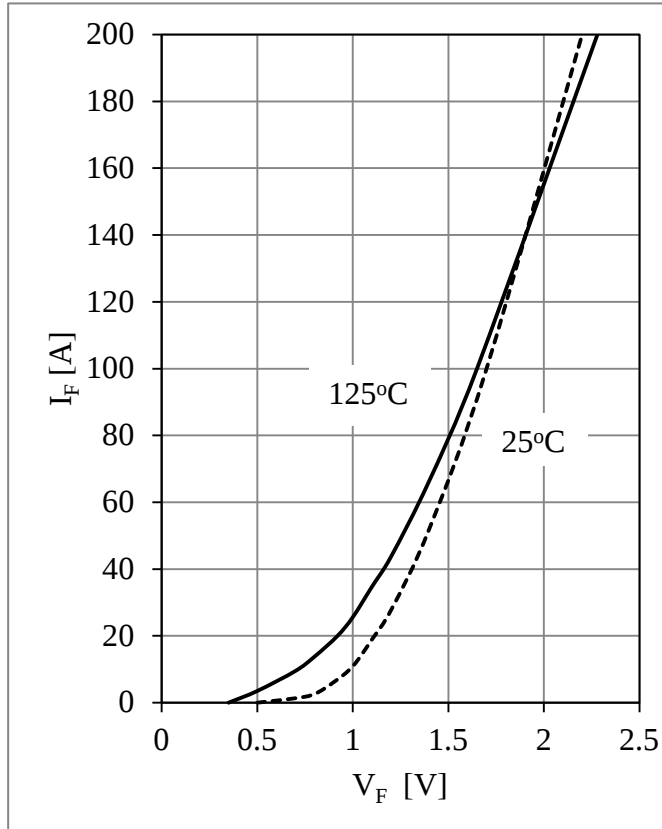
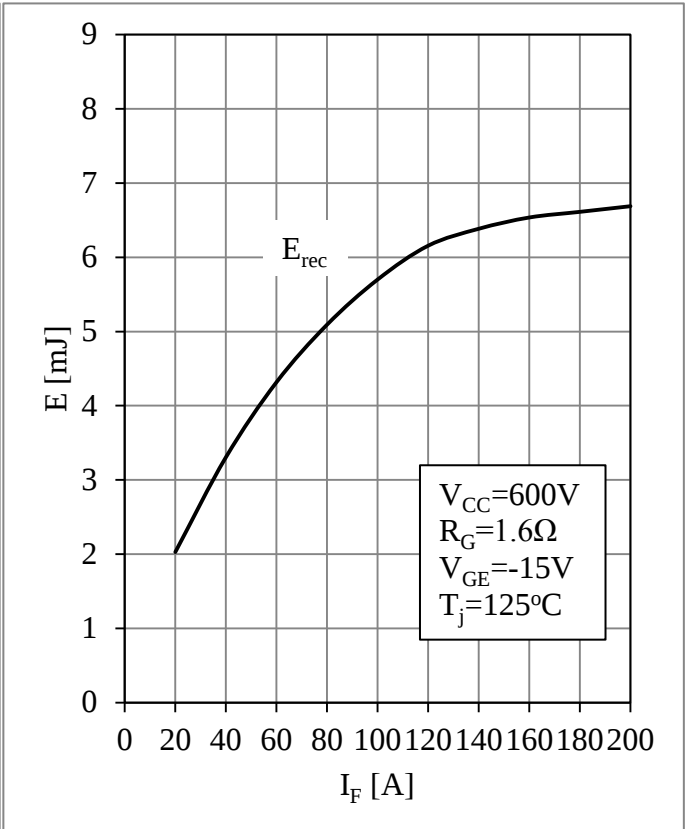


Fig 7. Diode Forward Characteristics

Fig 8. Diode Switching Loss vs.  $I_F$

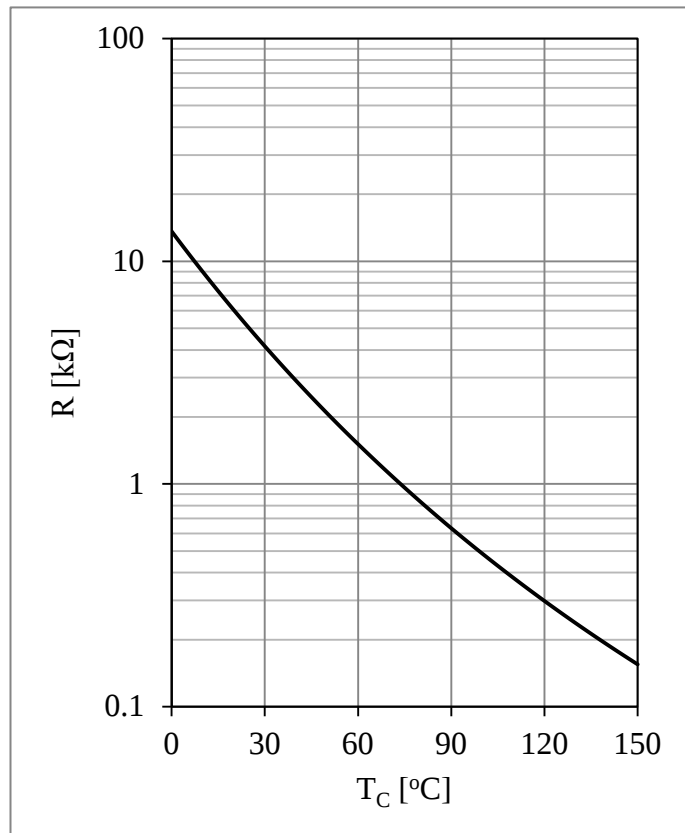
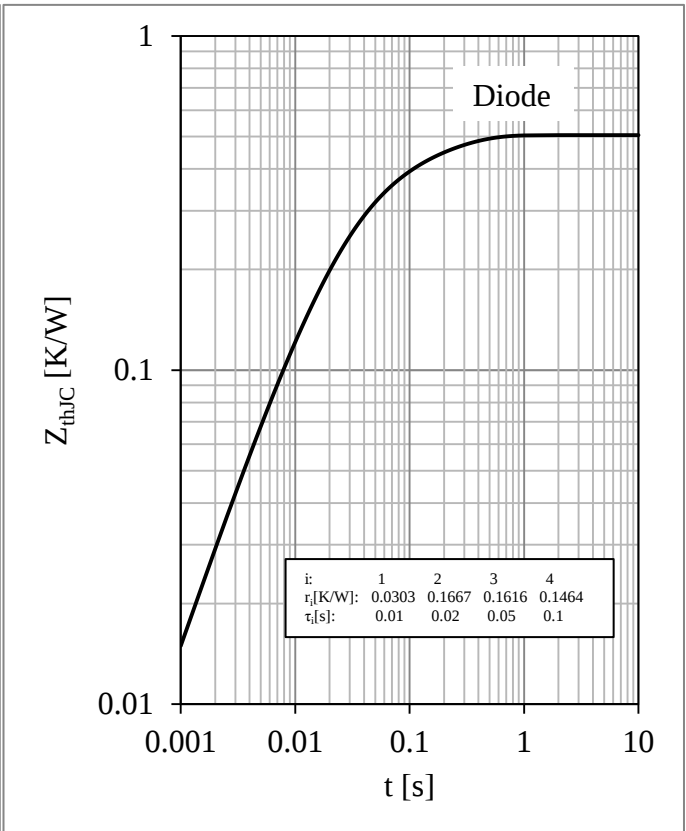
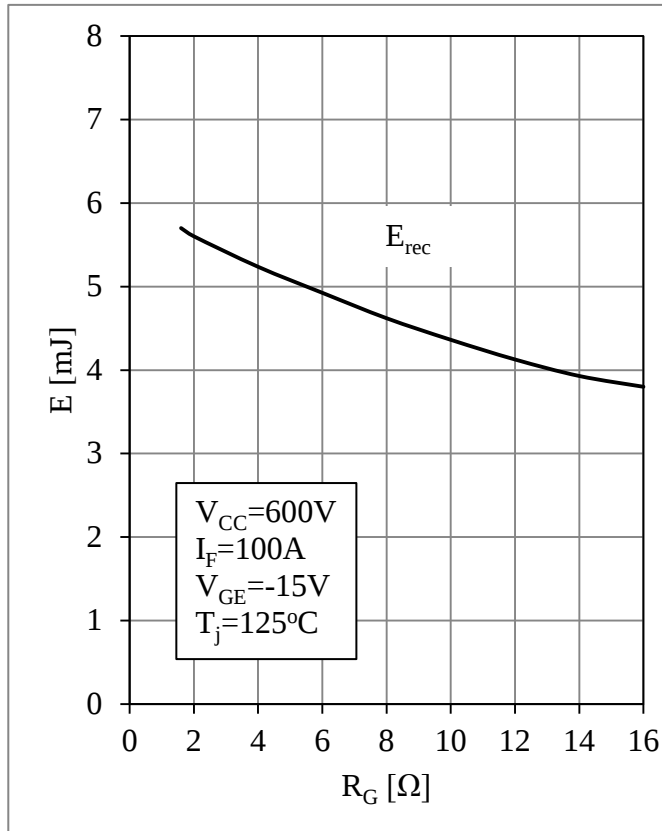
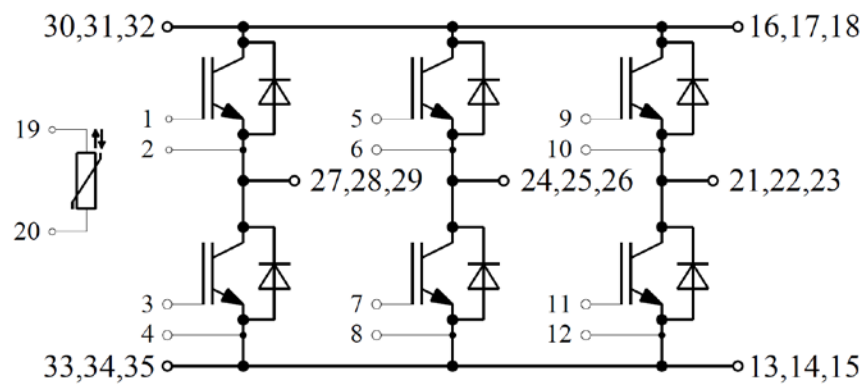


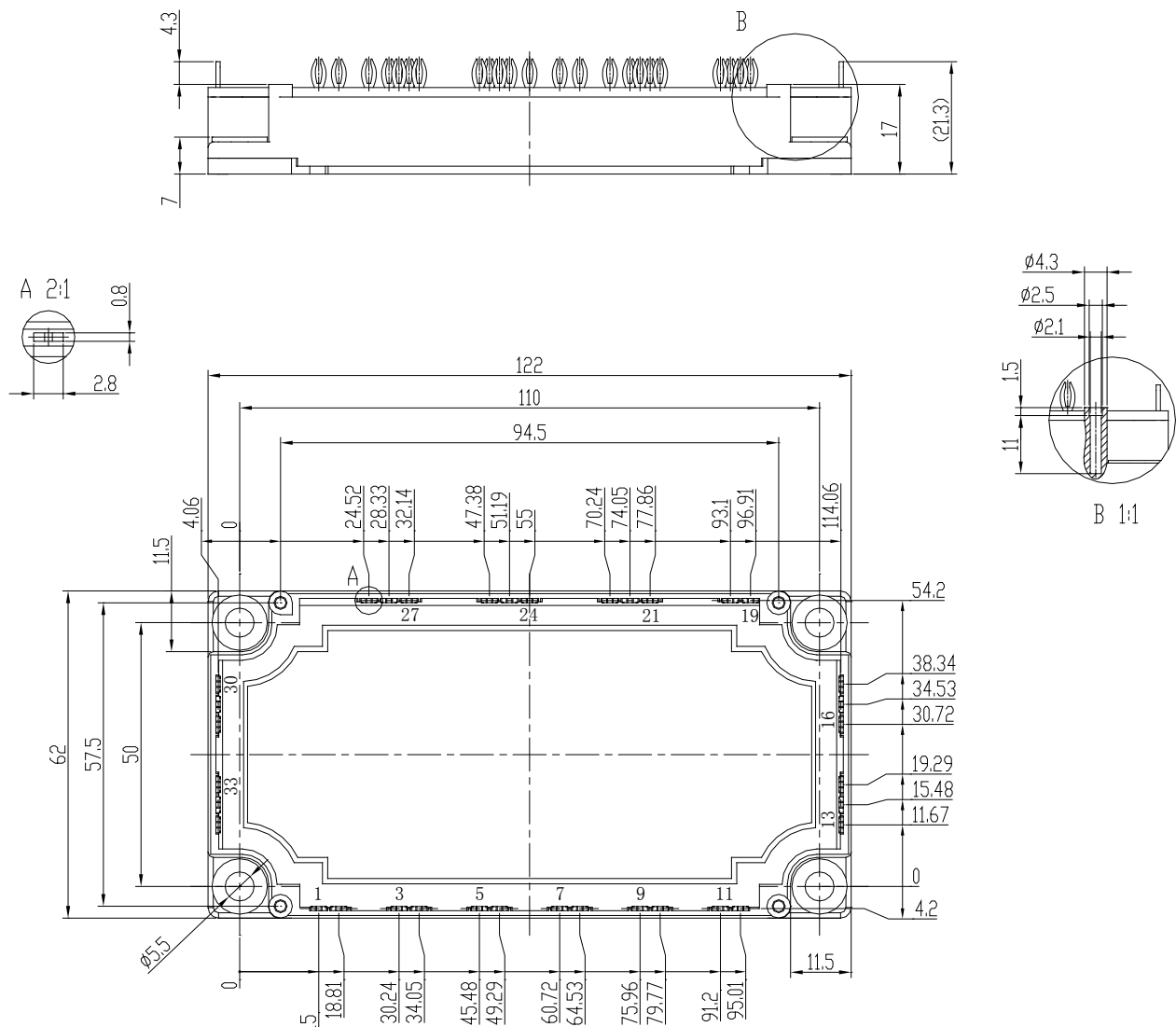
Fig 11. NTC Temperature Characteristic

## Circuit Schematic



## Package Dimensions

Dimensions in Millimeters



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